

**isc Silicon NPN Darlington Power Transistor**
**2SD2045**
**DESCRIPTION**

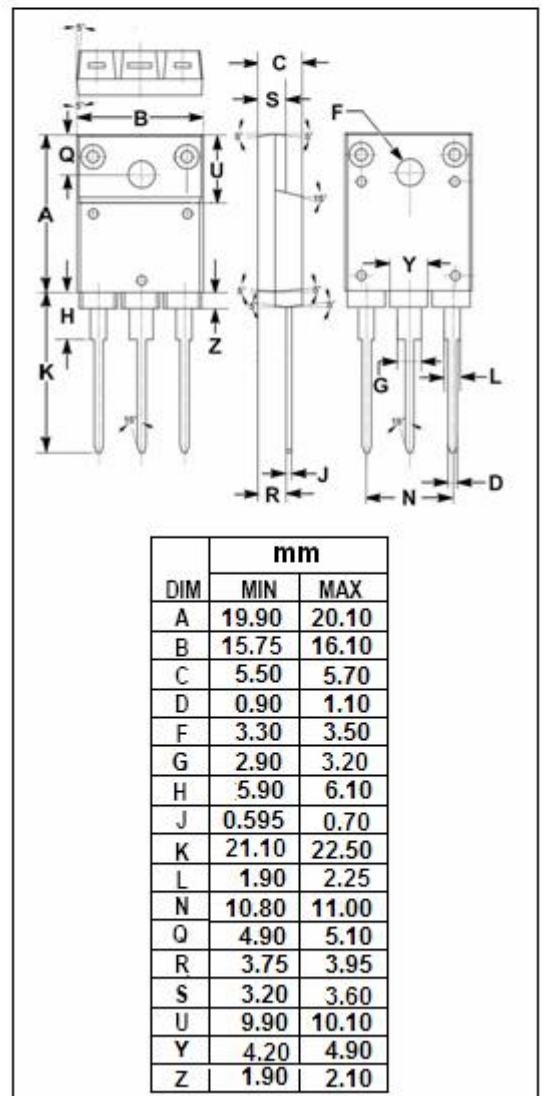
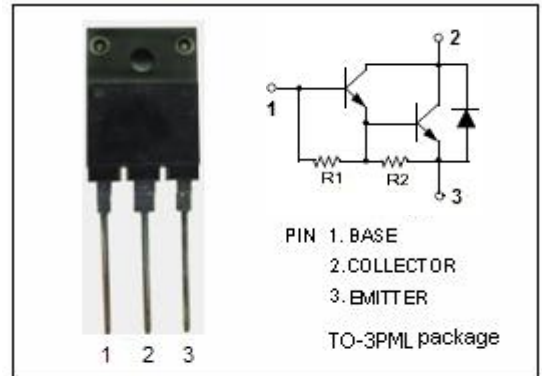
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 120V(\text{Min})$
- Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)} = 1.5V(\text{Max}) @ I_C = 3A$
- High DC Current Gain  
:  $h_{FE} = 2000(\text{Min}) @ I_C = 3A, V_{CE} = 2V$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed of driver of solenoid, motor and general purpose applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	120	V
$V_{CEO}$	Collector-Emitter Voltage	120	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	6	A
$I_{CM}$	Collector Current-Peak	10	A
$I_B$	Base Current-Continuous	1	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	50	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



## isc Silicon NPN Darlington Power Transistor

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## ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	120			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 3mA			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 3mA			2.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 120V; I <sub>E</sub> = 0			10	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			10	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 2V	2000			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>E</sub> = -1A; V <sub>CE</sub> = 12V		50		MHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V, f <sub>test</sub> = 1MHz		70		pF
Switching times						
t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 3A; I <sub>B1</sub> = I <sub>B2</sub> = 3mA; R <sub>L</sub> = 10 Ω ; V <sub>CC</sub> = 30V		0.5		μ s
t <sub>stg</sub>	Storage Time			5.5		μ s
t <sub>f</sub>	Fall Time			1.5		μ s

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